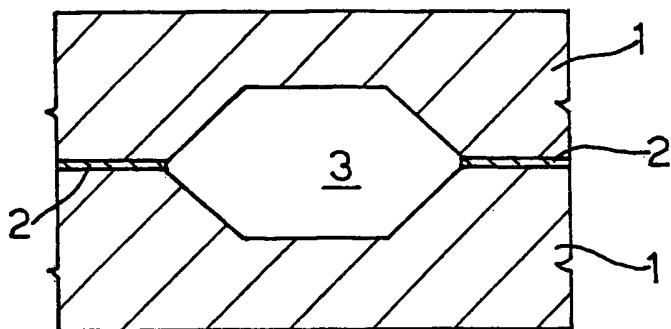
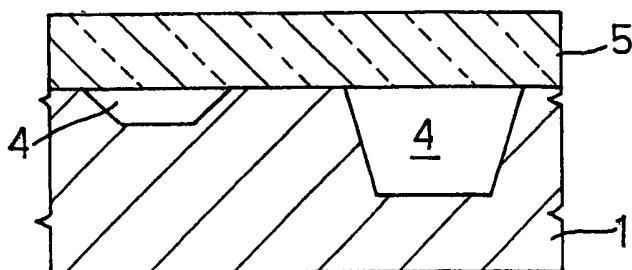


Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

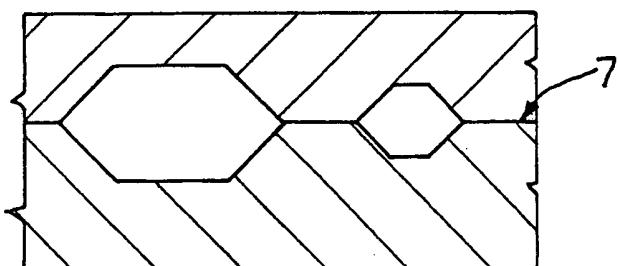
Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1



*FIG. 1
(Prior Art)*



*FIG. 2
(Prior Art)*



*FIG. 3
(Prior Art)*

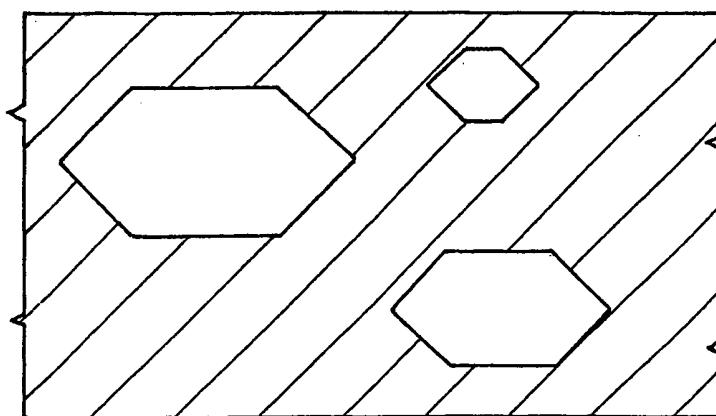


FIG. 4

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

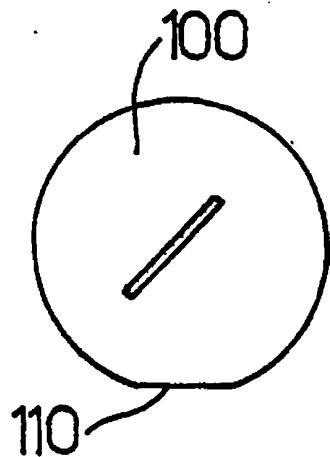


FIG. 5

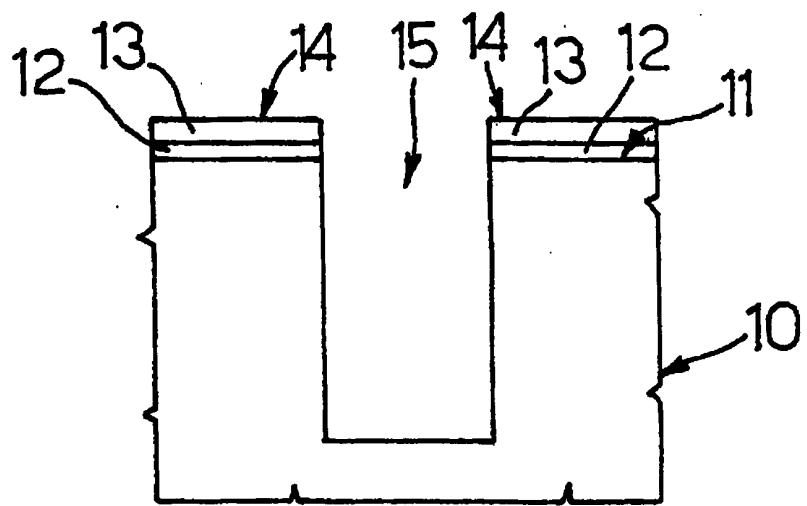


FIG. 6

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

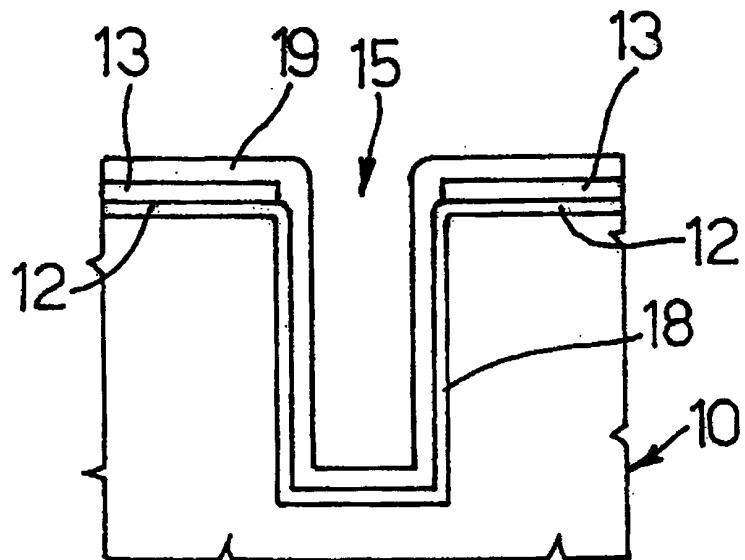


FIG. 7

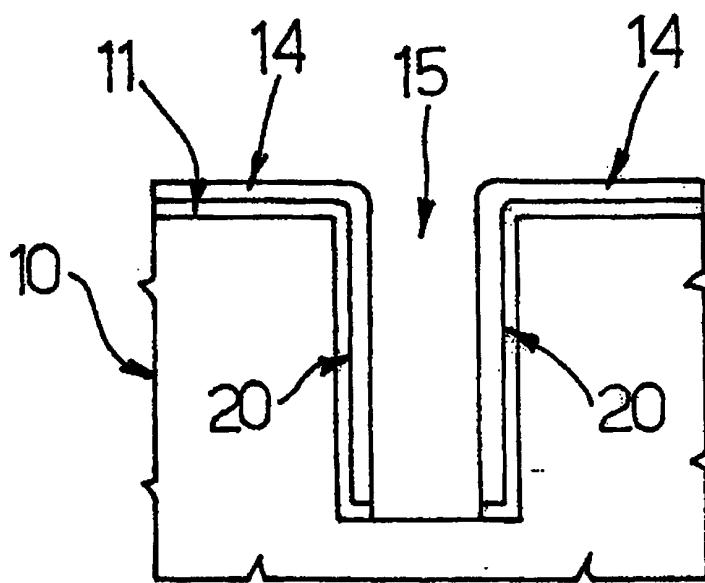


FIG. 8

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

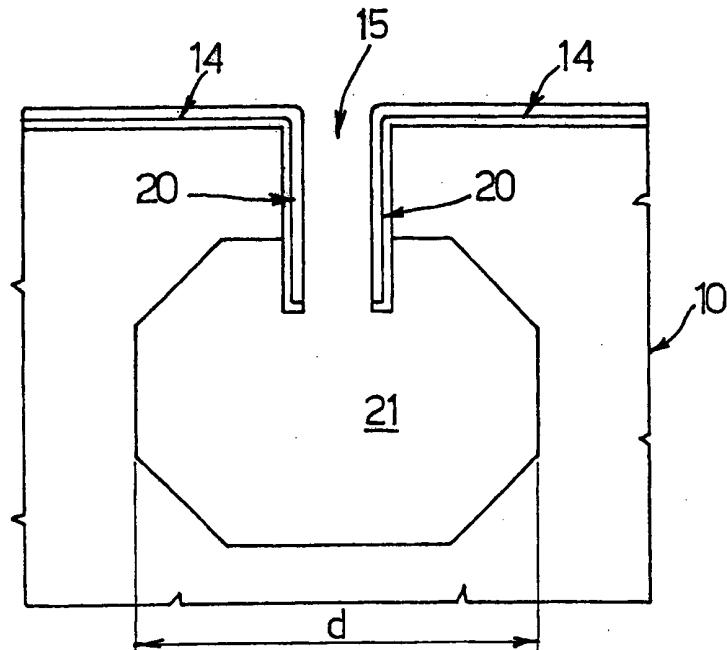


FIG. 9

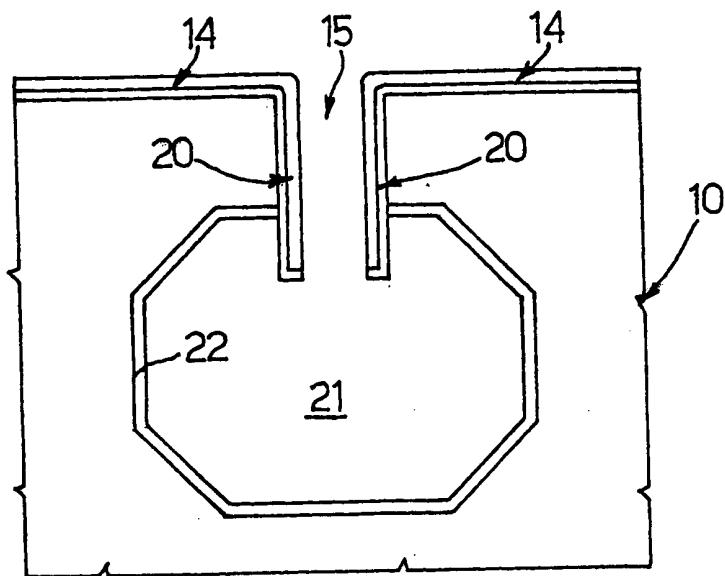


FIG. 10

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

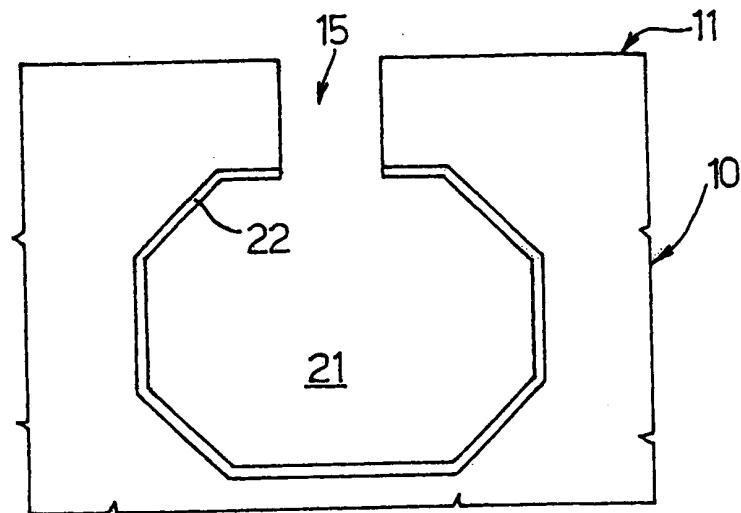


FIG. 11

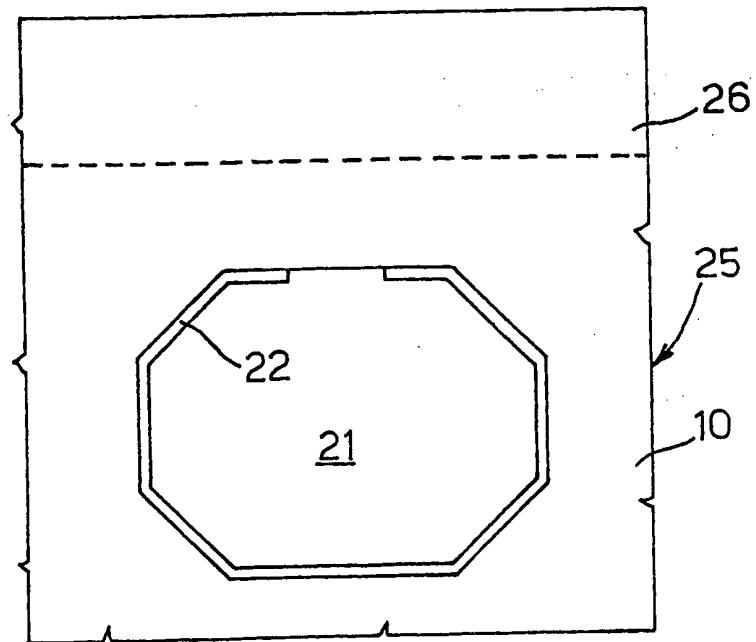


FIG. 12

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
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Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

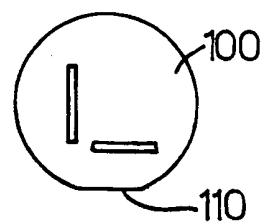


FIG. 13

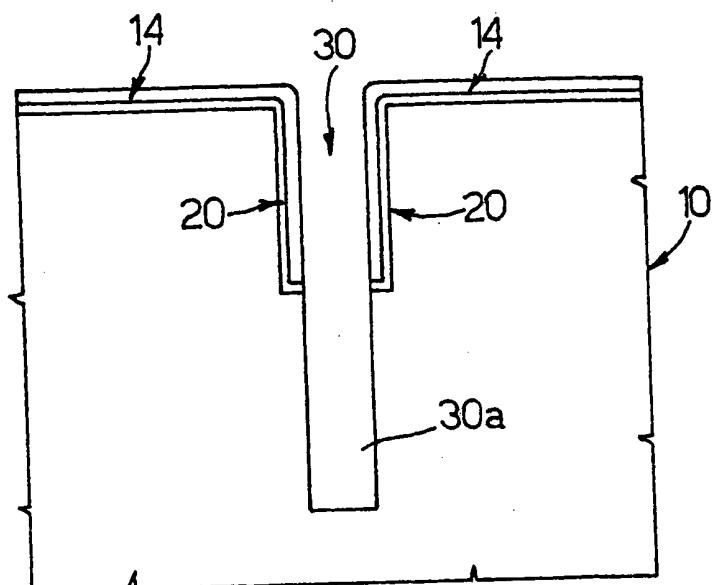


FIG. 14

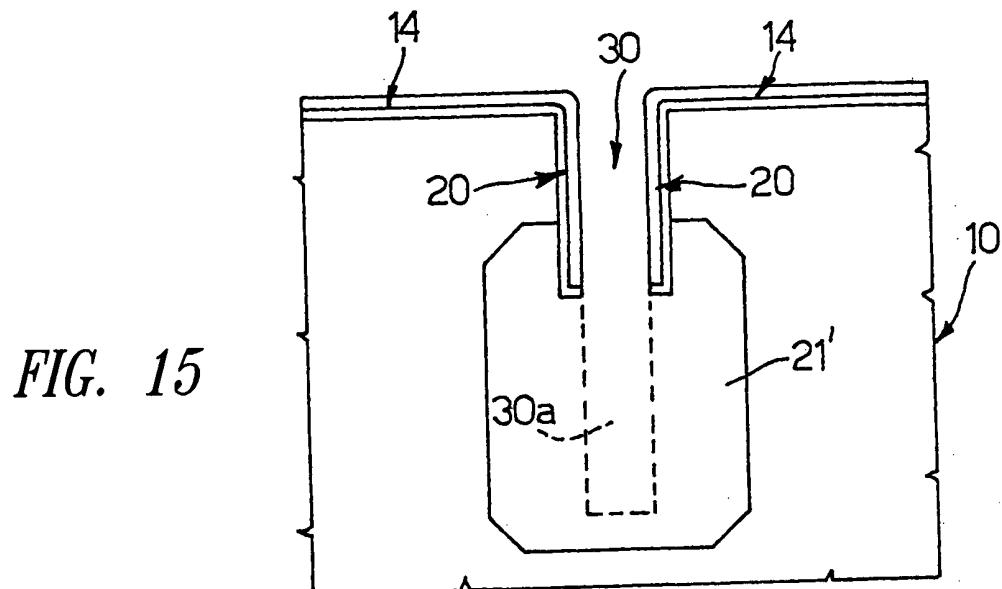
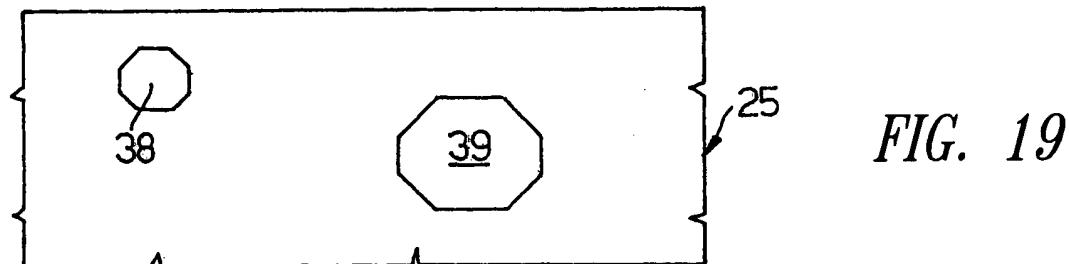
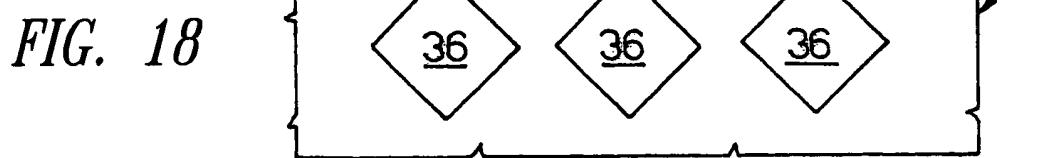
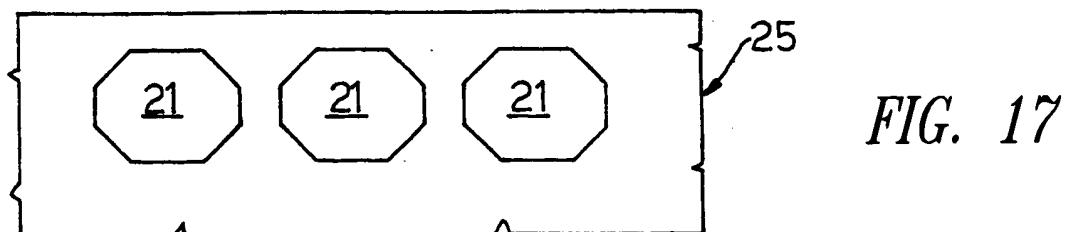
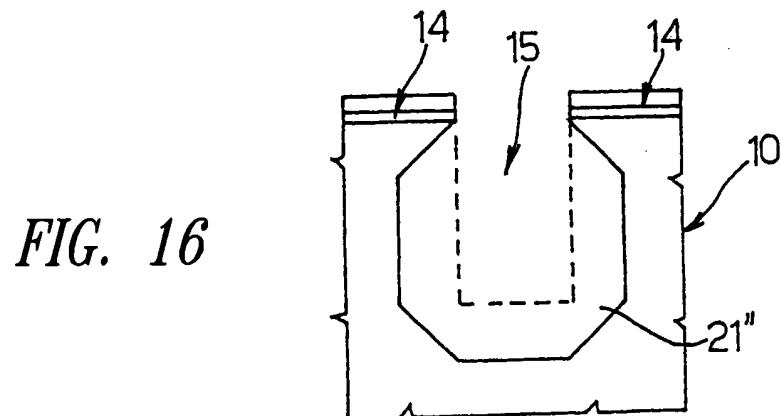


FIG. 15

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1



Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

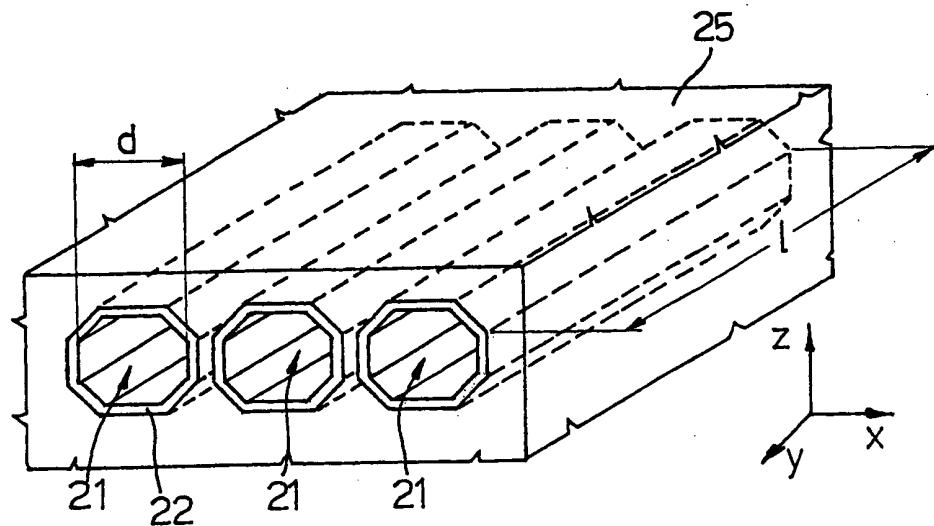


FIG. 20

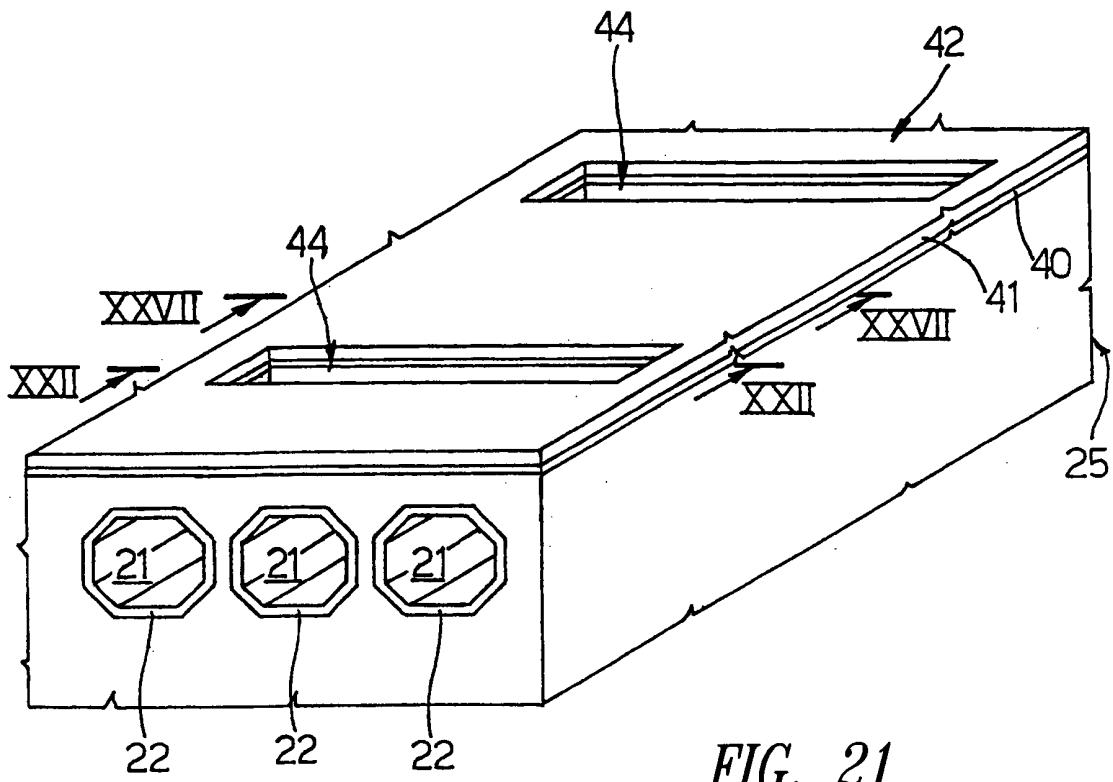


FIG. 21

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

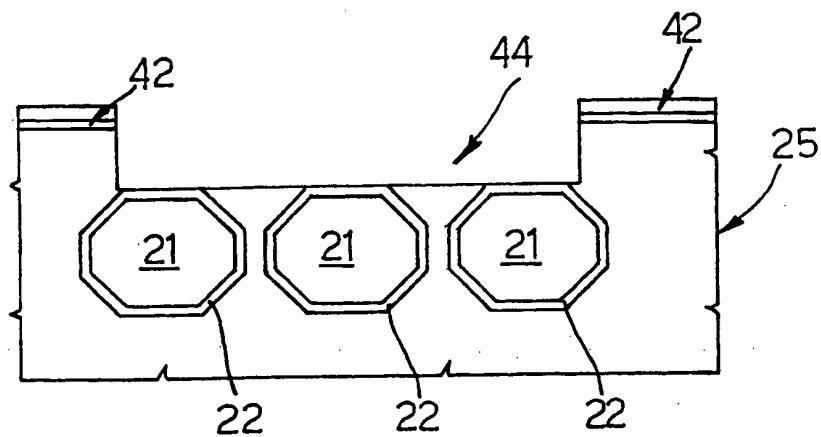


FIG. 22

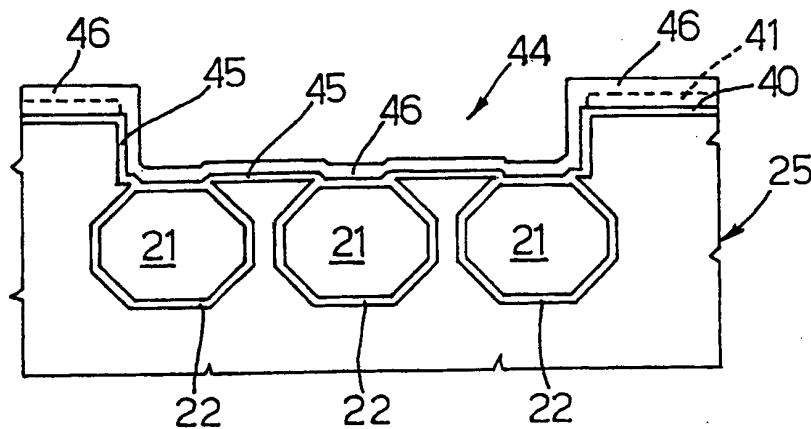


FIG. 23

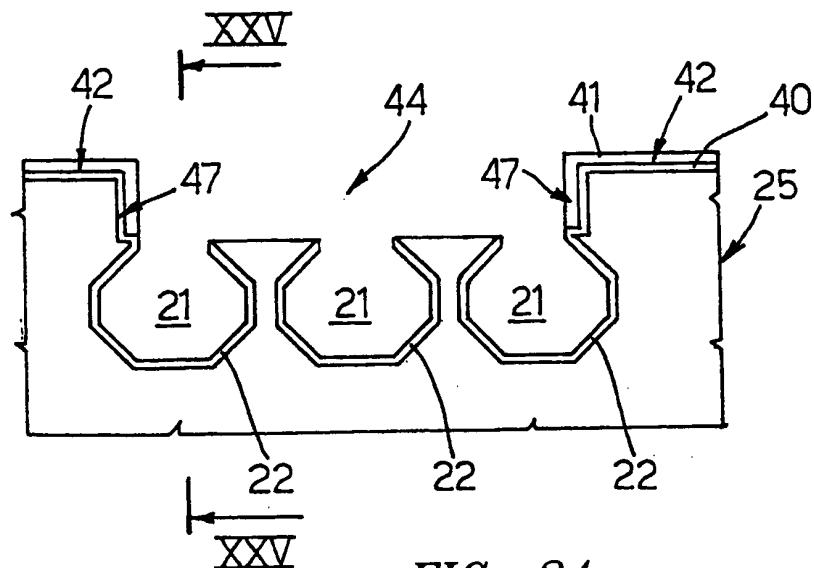


FIG. 24

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

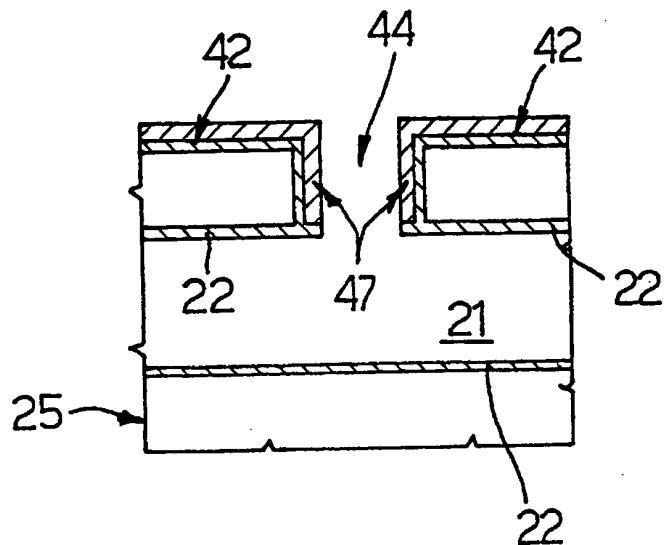


FIG. 25

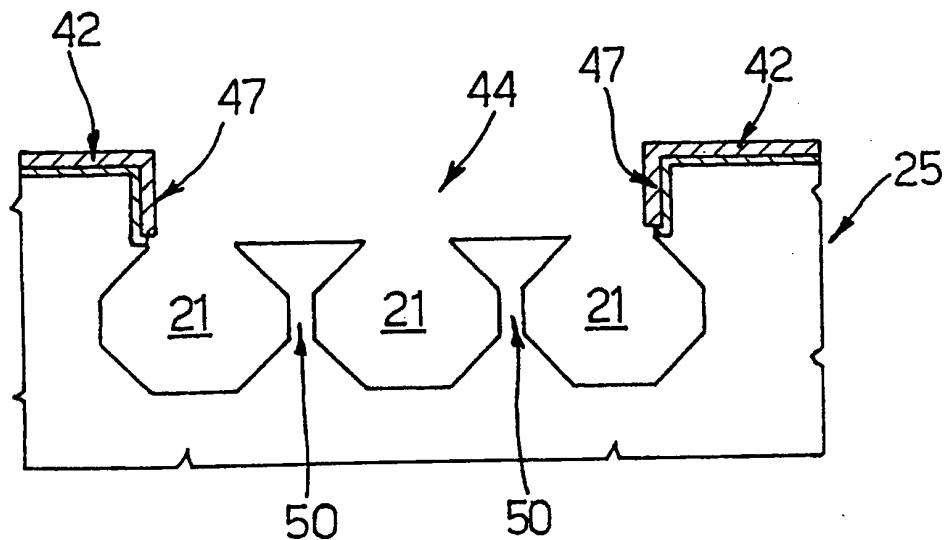


FIG. 26

Title: METHOD FOR FORMING HORIZONTAL BURIED CHANNELS OR CAVITIES IN WAFERS OF
MONOCRYSTALLINE SEMICONDUCTOR MATERIAL

Inventor(s): Gabriele Barlocchi et al. Express Mail No. EV336596659US Docket No. 854063.552D1

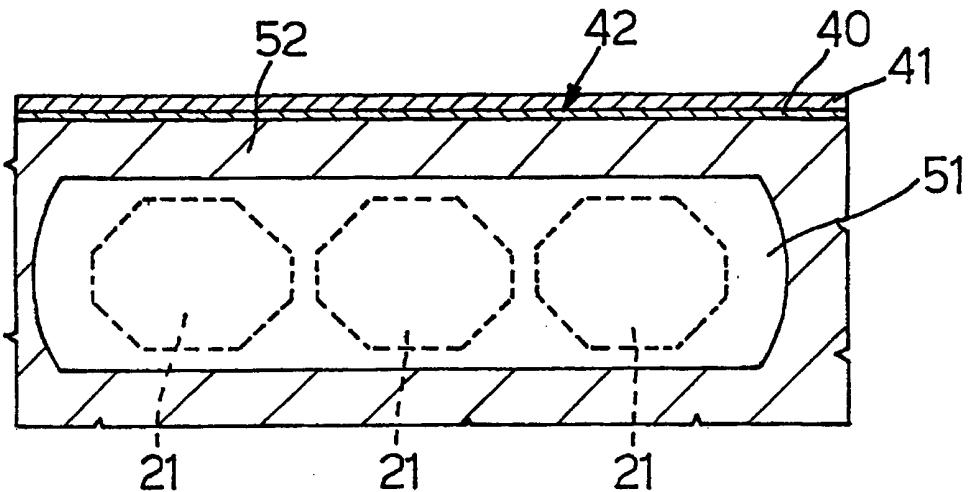


FIG. 27

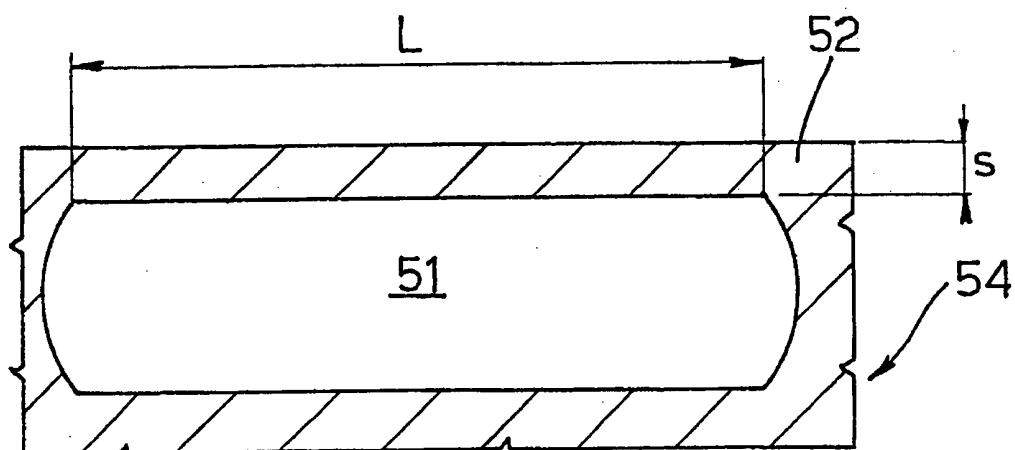


FIG. 28